



WANSEMI
万晶半导体

WP3080KA

Enhancement Mode N-Channel Power MOSFET

TO-252/NMOS/30V/±20V/1.6V/80A/4.2mΩ

Rev1.4



30V, 4.2mΩ, 80A, Single N-Channel

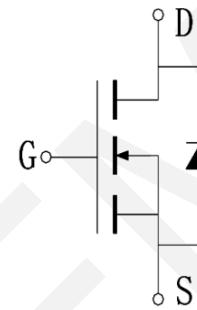
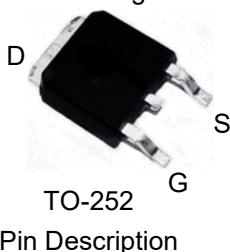
1. Features

- ◆ 30V MOSFET technology
- ◆ Low on-state resistance
- ◆ Fast switching
- ◆ $V_{GS} \pm 20V$

V_{DS}	$R_{DS(on)}$ Typ.	I_D Max.
30V	4.2mΩ @ 10V	80A
	6.4mΩ @ 4.5V	

2. Applications

- ◆ Power Switching Application
- ◆ Load Switching



Schematic Diagram

3. Package Marking and Ordering Information

Part no.	Marking	Package	PCS/Reel	PCS/CTN.
WP3080KA	WP3080KA	TO-252	2,500	25,000

4. Absolute Max Ratings at $T_a=25^\circ C$ (Note1)

Parameter	Symbol	Maximum	Units
Drain to Source Voltage	V_{DSS}	30	V
Gate to Source Voltage	V_{GSS}	± 20	V
Drain Current (DC)	I_D	80	A
Drain Current (Pulse), $PW \leq 300\mu s$	I_{DP}	280	A
Total Dissipation	P_D	50	W
Avalanche Energy, Single Pulsed	E_{AS}	144	mJ
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

**5.Thermal Resistance Ratings (Note 2)**

Parameter	Symbol	Value	Unit
Junction to case	R _{AJC}	2.5	°C/W

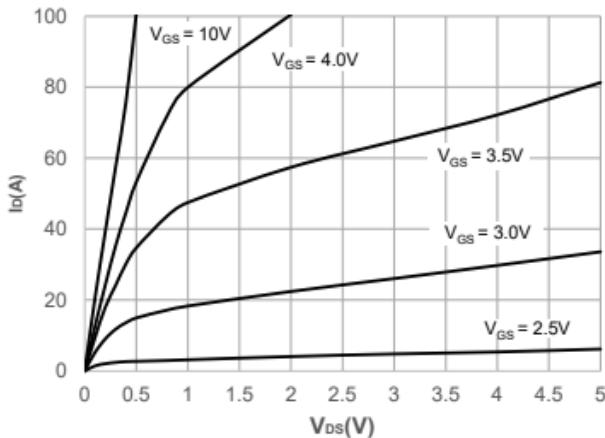
Note 2: When mounted on 1 inch square copper board $t \leq 10\text{sec}$ The value in any given application depends on the user's specific board design.

6.Electrical Characteristics at Ta=25°C (Note 3)

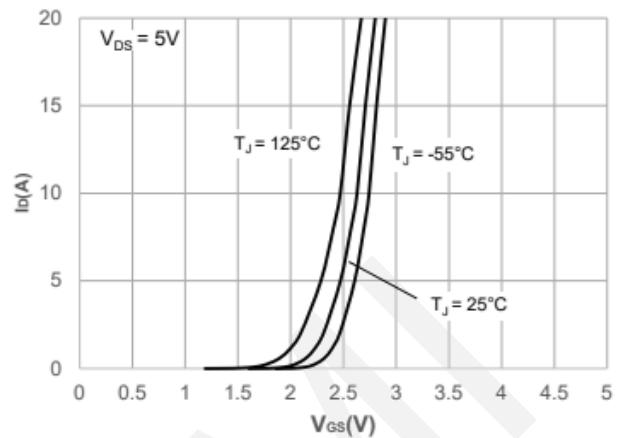
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain to Source Breakdown Voltage	V _{(BR)DSS}	I _D = 250μA, V _{GS} = 0V	30	-	-	V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30V, V _{GS} = 0V	-	-	1	μA
Gate to Source Leakage Current	I _{GSS1}	V _{GS} = ±20V, V _{SS} = 0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.1	1.6	2.5	V
Static Drain to Source On-State Resistance	R _{DS(on)}	I _D = 30A, V _{GS} = 10V	-	4.2	4.9	mΩ
		I _D = 20A, V _{GS} = 4.5V	-	6.4	7.9	mΩ
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =15V, Frequency=1.0MHz	-	1942	-	pF
Output Capacitance	C _{oss}		-	197	-	pF
Reverse Transfer Capacitance	C _{rss}		-	178	-	pF
Turn-ON Delay Time	t _{d(on)}	V _{DS} = 15V, I _D = 30A, V _{GS} = 10V, R _G = 3Ω	-	7	-	ns
Rise Time	t _r		-	14	-	ns
Turn-OFF Delay Time	t _{d(off)}		-	34	-	ns
Fall Time	t _f		-	11	-	ns
Total Gate Charge	Q _g	V _{DS} = 15V, V _{GS} = 10V, I _D = 30A	-	34	-	nC
	Q _{gs}		-	6.5	-	nC
	Q _{gd}		-	7.5	-	nC
Diode Forward Voltage	V _{FSD}	I _S = 30A, V _{GS} = 0V	0.4	0.89	1.2	V

Note 3: Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

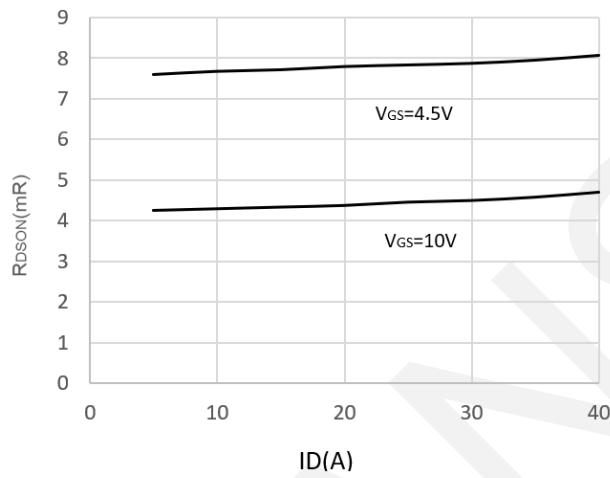
7.Typical electrical and thermal characteristics



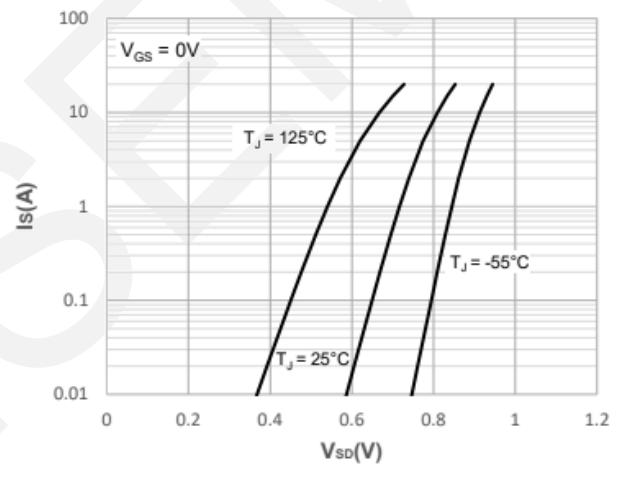
Output Characteristics



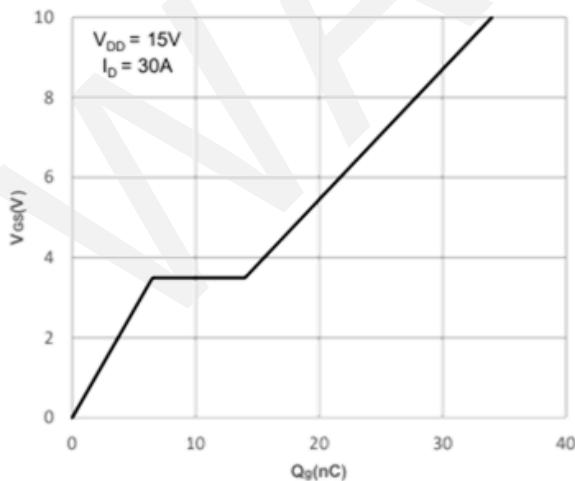
Typical Transfer Characteristics



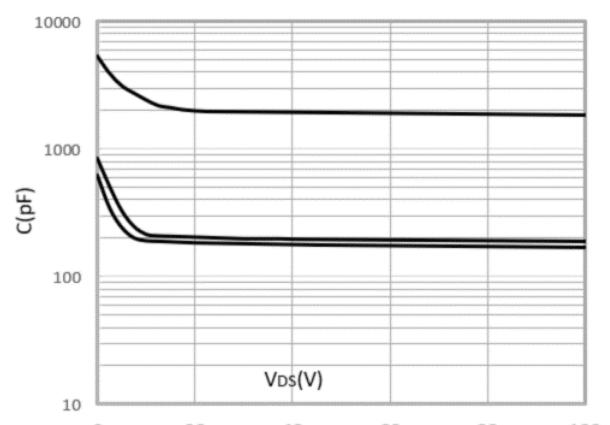
On-resistance vs. Drain Current



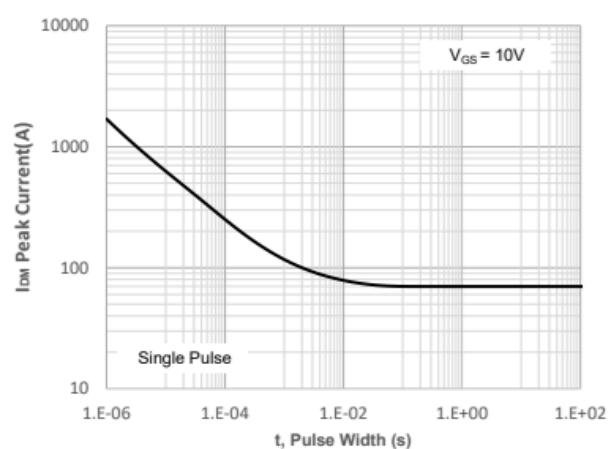
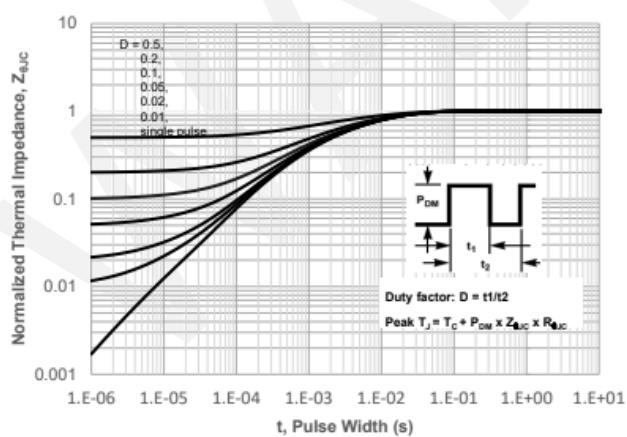
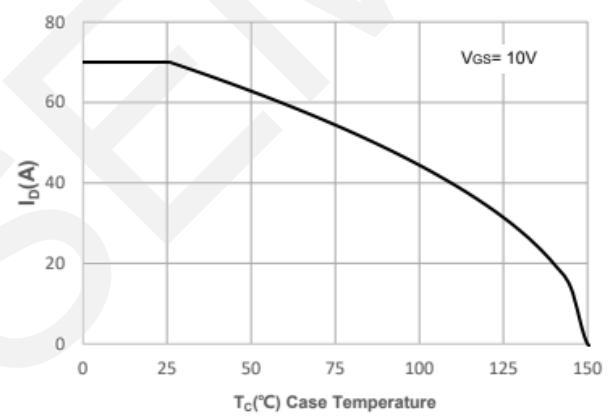
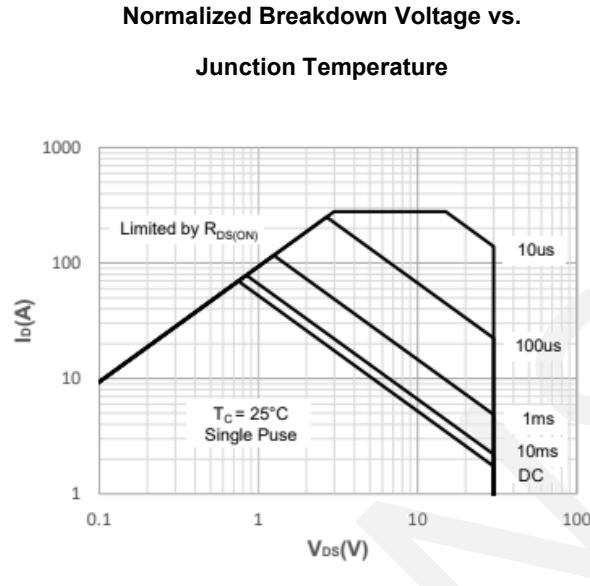
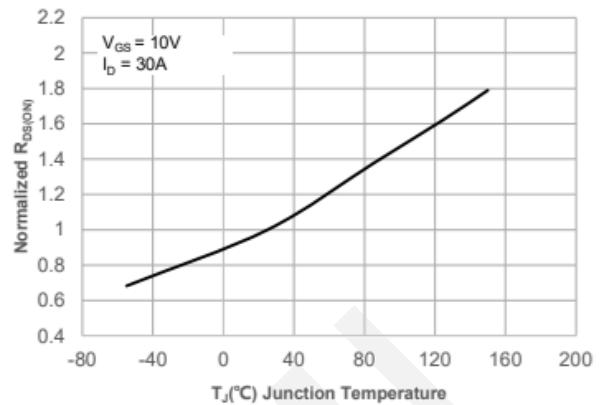
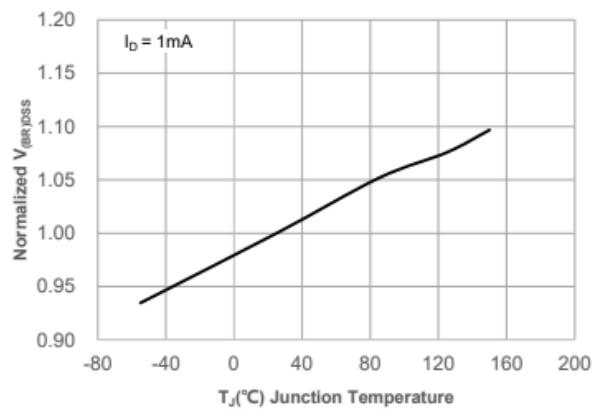
Body Diode Characteristics



Gate Charge Characteristics

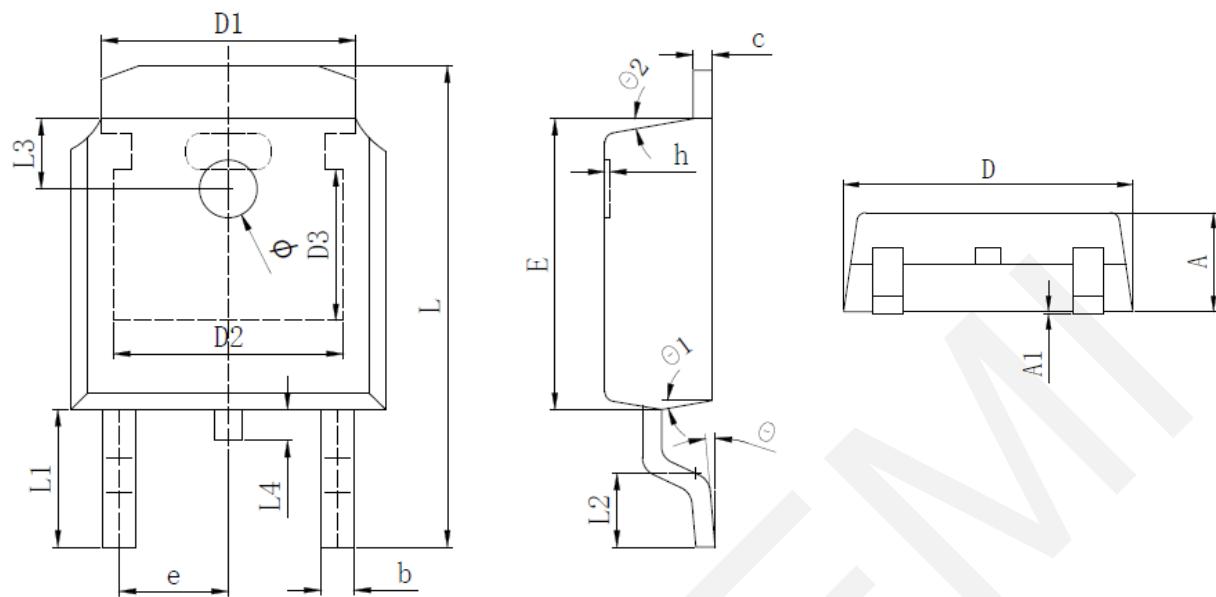


Capacitance Characteristics





8.Package Dimensions



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	2.200	2.300	2.400
A1	0.000		0.127
b	0.640	0.690	0.740
c (电镀后)	0.460	0.520	0.580
D	6.500	6.600	6.700
D1	5.334 REF		
D2	4.826 REF		
D3	3.166 REF		
E	6.000	6.100	6.200
e	2.286 TYP		
h	0.000	0.100	0.200
L	9.900	10.100	10.300
L1	2.888 REF		
L2	1.400	1.550	1.700
L3	1.600 REF		
L4	0.600	0.800	1.000
φ	1.100	1.200	1.300
θ	0°		8°
θ 1	9° TYP		
θ 2	9° TYP		

9. Important Notice

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